

2SK1030, 2SK1030A

Silicon N-channel Power F-MOS FET

■ Features

- Low ON resistance $R_{DS(on)} : R_{DS(on)} = 3.0\Omega$ (typ.)
- High switching rate : $t_i = 40ns$ (typ.)
- No secondary breakdown
- High breakdown voltage

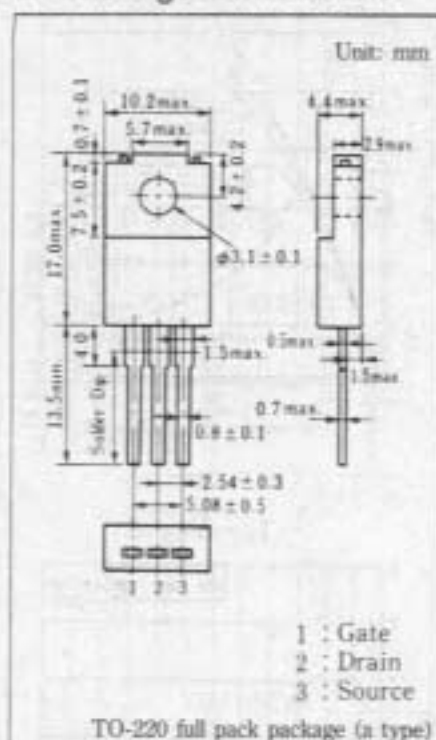
■ Application

- No contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching power source

■ Absolute Maximum Ratings ($T_c = 25^\circ C$)

Item	Symbol	Value	Unit
Drain-source voltage	V_{DS}	800	V
		900	
Gate-source voltage	V_{GS}	± 25	V
Drain current	DC	I_D	A
	Pulse to peak value	I_{DP}	
Power dissipation	$T_c = 25^\circ C$	P_D	W
	$T_a = 25^\circ C$		
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ C$

■ Package Dimensions



■ Electrical Characteristics ($T_c = 25^\circ C$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Drain current	I_{DS}	$V_{DS} = 640V, V_{GS} = 0$			0.1	mA
Gate-source current	I_{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0$			± 1	μA
Drain-source voltage	V_{DS}	$I_D = 1mA, V_{GS} = 0$	800			V
			900			
Gate threshold voltage	V_{th}	$V_{DS} = 25V, I_D = 1mA$	1		5	V
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2A$		3.0	5.0	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25V, I_D = 2A$	0.7	1.7		S
Input capacitance	C_{iss}	$V_{DS} = 20V, V_{GS} = 0, f = 1MHz$		600		pF
Output capacitance	C_{oss}			110		pF
Reverse transfer capacitance	C_{rss}			50		pF
Turn-on time	t_{on}	$V_{GS} = 10V, I_D = 2A$ $V_{DS} = 200V, R_L = 100\Omega$		55		ns
Fall time	t_i			40		ns
Delay time	$t_d(off)$			110		ns